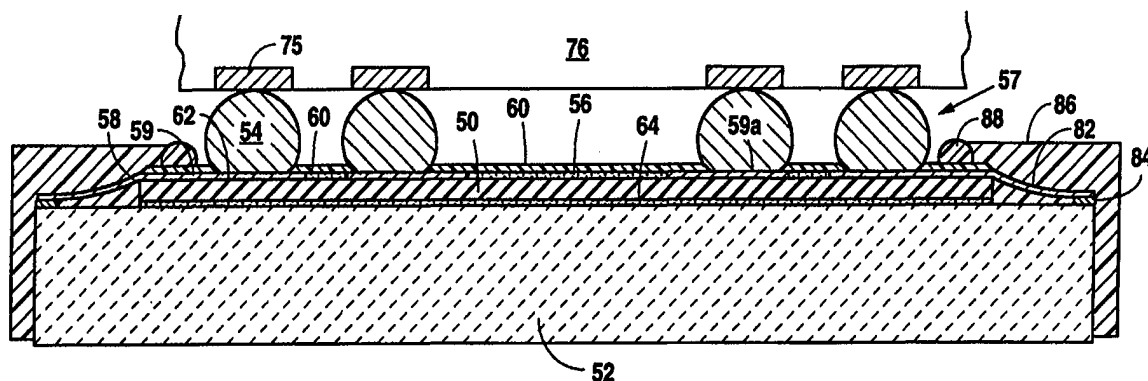




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<b>(21) International Application Number:</b> PCT/US97/05489 <b>(22) International Filing Date:</b> 2 April 1997 (02.04.97)  <b>(30) Priority Data:</b> 08/759,253                      2 December 1996 (02.12.96)                      US  <b>(71) Applicant:</b> MINNESOTA MINING AND MANUFACTURING COMPANY [US/US]; 3M Center, P.O. Box 33427, Saint Paul, MN 55133-3427 (US).  <b>(72) Inventors:</b> SCHUELLER, Randolph, D.; P.O. Box 33427, Saint Paul, MN 55133-3427 (US). GEISSINGER, John, D.; P.O. Box 33427, Saint Paul, MN 55133-3427 (US).  <b>(74) Agents:</b> MCNUTT, Matthew, B. et al.; Minnesota Mining and Manufacturing Company, Office of Intellectual Property Counsel, P.O. Box 33427, Saint Paul, MN 55133-3427 (US).		<b>(81) Designated States:</b> AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, CA, CH, CN, CU, CZ, DE, DK, EE, ES, FI, GB, GE, GH, HU, IL, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MD, MG, MK, MN, MW, MX, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, TJ, TM, TR, TT, UA, UG, UZ, VN, YU, ARIPO patent (GH, KE, LS, MW, SD, SZ, UG), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, ML, MR, NE, SN, TD, TG).  <b>Published</b> <i>With international search report.</i>

(54) Title: CHIP SCALE BALL GRID ARRAY FOR INTEGRATED CIRCUIT PACKAGE



## (57) Abstract

A chip scale ball grid array for integrated circuit packaging having a nonpolymer layer (50) or support structure positioned between a semiconductor die (52) and a substrate (76). The nonpolymer support structure acts to increase circuit reliability by reducing thermal stress effects and/or by reducing or eliminating formation of voids in an integrated circuit package. A nonpolymer support structure may be a material, such as copper foil, having sufficient rigidity to allow processing of chip scale package in strip format.

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**CHIP SCALE BALL GRID ARRAY  
FOR INTEGRATED CIRCUIT PACKAGE**

**BACKGROUND OF THE INVENTION**

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1. Field of the Invention

This invention relates generally to integrated circuit packaging, and more specifically to ball grid arrays. In particular, this invention relates to a  
10 chip scale ball grid array design employing a flex tape having a nonpolymer support structure.

2. Description of the Related Art

The demand for a reduction in size and an increase  
15 in sophistication of electronic components has driven the industry to produce smaller and more complex integrated circuits (ICs). These same trends have forced IC packages to have smaller footprints, higher lead counts and better electrical and thermal  
20 performance. At the same time, these IC packages are also required to meet accepted reliability standards.

With reduction in device sizes and corresponding increase in circuit complexity, integrated circuit packages are required to have smaller footprints,  
25 higher lead counts and higher electrical and thermal performance. At the same time, integrated circuit packages are also required to meet accepted reliability standards.

Ball grid array (BGA) packages were developed to  
30 meet the demand for integrated circuit packages having higher lead counts and smaller footprints. A BGA package is typically a square package with terminals, normally in the form of an array of solder balls, protruding from the bottom of the package. These  
35 terminals are designed to be mounted onto a plurality

of bonding pads located on the surface of a printed circuit board (PCB) or other suitable substrate.

Recently, BGA packages have been fabricated using a tape automated bonding (TAB) process and flexible circuitry (sometimes referred to as TAB tape) which typically consists of copper traces on a thin polyimide substrate. Electrically conductive leads may be laminated on one or both sides of the TAB tape. This BGA design is commonly referred to as a Tape BGA (TBGA). In a TBGA design, the circuitry on the tape has leads which are connected to a semiconductor die through any of the conventional methods such as wire bonding, thermocompression bonding, or flip chips. If the circuitry is present on both sides of the tape, electrically conducting vias may extend through the tape from one layer of circuitry to another.

For some applications such as portable electronic components (cellular phones, disk drives, pagers, etc.), even BGA packages are sometimes too large. Consequently, solder bumps are sometimes deposited directly onto the surface of an IC itself and used for attachment to the PCB (commonly referred to as direct chip attach or flip chip). However, there are a number of problems associated with this approach. First, the deposition of solder balls requires a number of costly process steps. In addition, it is typically necessary to deposit a polymer underfill beneath a die to achieve acceptable reliability with flip chip attach to a PCB. This underfill is required to reduce thermal stress which is caused by the low thermal expansion of a die relative to the typically much higher expansion of a PCB ("thermal mismatch stress"). Deposition of this underfill is a costly process which eliminates the ability to rework the component. Consequently, if any defects are found, a valuable PCB must be thrown out.

To address concerns associated with flip chip processing, another class of BGA packages have been developed. This class of BGA package may be referred to as a chip scale ball grid array or a chip scale package (CSP). Chip scale packages are so called because the total package size is similar or not much larger than the size of the IC itself. In a chip scale package, solder ball terminals are typically disposed underneath a semiconductor die in order to reduce package size. One example of a CSP is a product developed by TESSERA called "MICRO BGA." This product consists of a flexible circuit with a soft compliant elastomer layer (or elastomer pad) between the die and the circuit. This elastomeric member consists of polymer materials such as silicone and is typically about 5-7 mils thick. One purpose of the elastomer is to obtain suitable reliability by minimizing thermal mismatch stress between the die and the PCB without the need for expensive underfill material.

Although current chip scale package designs offer improved board space utilization and ease of surface mount assembly, these products suffer from a number of shortcomings. First, it is often difficult to find a suitable elastomer material which meets industry requirements of low moisture absorption, low outgassing, and the ability to withstand cleaning solvents commonly used in the industry. For example, silicone is known to breakdown with some typically used cleaning solvents, and polymer materials in general tend to absorb and outgas moisture. If moisture absorption is too high, rapid outgassing of this moisture at reflow temperatures will cause voids to form at component interfaces and even bursting of the package. For example, moisture may release from polymer materials in a tape and become trapped within the die attachment adhesive. Voids may then be formed

when this trapped moisture expands during board assembly heating operations, typically causing cracking and package failure. Formation of such voids may be particularly acute during reflow attachment to a PCB.

5           Another significant challenge with chip scale package designs is the process for attaching the elastomer to the flex tape. One method commonly employed is to pick and place elastomer pads onto individual sites while another method involves screen  
10       printing a fluid polymer followed by a cure. In either case, it is difficult to meet the tight tolerances required for a CSP application. Yet another concern is package flatness. In a typical CSP design, it is critical that the package flatness (coplanarity) be  
15       less than about 1 mil to ensure that all solder balls contact the PCB upon reflow. This level of flatness or coplanarity may be difficult to achieve with soft polymer and elastomer materials commonly used. Finally, if a die is not adequately isolated from other  
20       parts of a package, premature failure of solder ball joints may occur due to thermal stress generated between an assembled die and a substrate, such as a circuit board.

          It is often desired to handle IC packages in strip  
25       format since a great deal of equipment currently exists for handling this configuration. For example, lead frames for quad flat packs have typically been processed in strips of four to eight units. Plastic BGA packages and some TBGA packages have also been  
30       produced in strip format for easy handling through the assembly process. Such strips are loaded into magazines which are used to feed assembly equipment for die attach, wire bonding, overmolding/encapsulating, solder ball attach, and other processing steps.  
35       Although some assemblers may desire to perform these processes in a reel to reel fashion, many may prefer

the conventional strip format. However, conventional CSP designs employing elastomer pads lack sufficient rigidity for conventional strip format processing without some additional source of rigidity. For  
5 example, the TESSERA "MICRO BGA" design employs a metal frame adhered to the outer edge of a strip of parts to allow strip format processing. The use of such frames is not convenient and adds to the final cost of a product because it increases the complexity and number  
10 of components in a tape processing design, as well as requires additional steps to attach and remove the frames during processing. Therefore, although strip format processing has typically been used for integrated circuit packaging, no convenient strip  
15 format chip scale package design current exists.

In other CSP designs, elastomer pads have been directly laminated to circuitry and semiconductor dies without using layers of adhesive in an effort to eliminate void formation in adhesive layers. However,  
20 these designs still may suffer from thermal stress problems and do not possess sufficient rigidity for strip format processing.

In still other CSP designs, such as the TEXAS INSTRUMENTS "MICRO STAR BGA," an IC is adhered directly  
25 to the surface of a flex circuit without a polymer or elastomer pad. This structure does not decouple the die from the PCB, consequently, an expensive underfill material is required to achieve the required reliability in the solder joints. In addition, it has  
30 been found that moisture from polymer materials employed in this design outgasses during curing of the die attach adhesive, causing voids in the adhesive.

Consequently, a need exists for a low cost and solvent resistant chip scale package which has  
35 sufficient coplanarity, and which does not suffer from moisture and thermal stress related problems. A need

also exists for a chip scale package which may be easily produced in strip format.

5     **SUMMARY OF THE INVENTION**

          The disclosed method and apparatus relate to chip scale ball grid arrays for integrated circuit packaging. These products may be used to provide low  
10    cost chip scale packages that offer improved reliability and which facilitate processing.

          In the disclosed embodiments, a nonpolymer layer or support structure is used between a semiconductor die and accompanying circuitry. When employed as a  
15    support structure, a nonpolymer layer may be used to provide a substantially rigid and planar surface, as well as to separate or decouple the die from a substrate, such as a printed circuit board (PCB). In a typical embodiment, adhesive materials are also  
20    employed between a nonpolymer support structure and adjacent components of a chip scale package assembly for purposes of attachment and to further decouple a die and substrate. By decoupling a die and substrate, the nonpolymer support structure reduces thermal  
25    stress. Because the support structure is nonpolymeric, void creation between the support structure and a die is substantially eliminated. The nonpolymer support structure also offers sufficient rigidity to allow integrated circuit processing in strip formats. When  
30    employed as a layer that is thinner and less rigid than a support structure layer, nonpolymer material acts to substantially eliminate the formation of voids, among other things.

          In one aspect, this invention is a package for an  
35    integrated circuit including an intermediate circuit



having an array of electrical interconnects and at least one nonpolymer layer having first and second sides. The first side of the nonpolymer layer is structurally coupled to the integrated circuit, and the  
5 second side of the nonpolymer layer is structurally coupled to the intermediate circuit.

In another aspect, this invention is a method of forming a package for an integrated circuit including the steps of providing an intermediate circuit  
10 including an array of electrical interconnects, and providing at least one nonpolymer layer having a first side adapted for structural coupling to an integrated circuit. This method also includes the step of structurally coupling the second side of the nonpolymer  
15 layer to the intermediate circuit.

In another aspect, this invention is an electronic package including a flexible tape having a patterned conductive layer and at least one patterned dielectric layer. The package also includes at least one  
20 nonpolymer support structure having first and second sides. The first side of the support structure is structurally coupled to the second side of the conductive layer of the flexible tape.

In another aspect this invention is an electronic  
25 package, including a patterned conductive layer having first and second sides and an outer lateral boundary. The conductive layer is patterned to form an electrically conductive region having peripheral conductive features disposed around a circumference of  
30 the outer lateral boundary for electrical connection to a semiconductor device. The package also includes a patterned dielectric layer having first and second sides and an outer lateral boundary with a smaller circumference than the circumference of the patterned  
35 conductive layer. The dielectric layer is patterned to form a plurality of openings extending through the

dielectric layer, with each of the openings being configured to receive a solder ball. The first side of the conductive layer is joined to the second side of the dielectric layer so that the plurality of openings  
5 in the dielectric layer are aligned with at least part of the electrically conductive region of the conductive layer, and so that the peripheral conductive features of the conductive layer extend beyond the outer boundary of the dielectric member. Also provided is a  
10 substantially rigid nonpolymer support structure having first and second sides, and having an elastic modulus greater than about 1 Mpsi. The first side of the support structure is structurally coupled to the second side of the conductive layer. The first side of a  
15 semiconductor device is structurally coupled to the second side of the nonpolymer support structure. The semiconductor device includes a plurality of electrical contact sites, with at least one of the contact sites being electrically coupled to the peripheral conductive  
20 features of the conductive layer. A plurality of solder balls are disposed on the first side of the dielectric layer, with each of the solder balls positioned in one of the plurality of openings in the dielectric layer and electrically connected to the  
25 conductive region of the conductive layer.

#### BRIEF DESCRIPTION OF THE DRAWINGS

30 FIG. 1 is a cross-sectional representation of a conventional chip scale package design of the prior art.

FIG. 2 is a cross-sectional representation of another conventional chip scale package design of the prior art.

5        FIG. 3 is a cross-sectional representation of a chip scale package design according to one embodiment of the disclosed method and apparatus.

10       FIG. 3A is a cross-sectional representation of another chip scale package design according to one embodiment of the disclosed method and apparatus.

15       FIG. 3B is a cross-sectional representation of another chip scale package design according to one embodiment of the disclosed method and apparatus.

20       FIG. 3C is a cross-sectional representation of another chip scale package design according to one embodiment of the disclosed method and apparatus.

FIG. 3D is a cross-sectional representation of another chip scale package design according to one embodiment of the disclosed method and apparatus.

25       FIG. 4 is a cross-sectional representation illustrating lamination of adhesive layers to a thin nonpolymer material according to one embodiment of the disclosed method and apparatus.

30       FIG. 5 is a top view of a sheet of nonpolymer material that has been laminated with adhesive and punched according to one embodiment of the disclosed method and apparatus.

FIG. 6 is a top view of the nonpolymer sheet of FIG. 5 with laminated flex circuitry according to one embodiment of the disclosed method and apparatus.

5        FIG. 6A is a top view of the nonpolymer sheet of FIG. 5 with an attached wire bonded die according to one embodiment of the disclosed method and apparatus.

10       FIG. 7 is a cross-sectional representation of a chip scale package strip positioned in a fixture for bonding according to one embodiment of the disclosed method and apparatus.

15       FIG. 8 is a cross-sectional representation of a chip scale package strip positioned in a fixture during overmolding according to one embodiment of the disclosed method and apparatus.

20       FIG. 9 is a cross-sectional representation of a chip scale package strip oriented die-side upwards on a fixture for encapsulation according to one embodiment of the disclosed method and apparatus.

25       FIG. 10 is a cross-sectional representation of a completed chip scale package according to one embodiment of the disclosed method and apparatus.

30       **DESCRIPTION OF SPECIFIC EMBODIMENTS**

FIG. 1 illustrates a conventional chip scale package integrated circuit package design having an elastomer pad 10 placed between a semiconductor die 12 and two piece flexible circuit tape 18. The elastomer pad 10 is often applied as part of a tape and may have

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adhesive layer **16** and adhesive layer **24** disposed on each side. A two piece tape is often employed, although tape having three or more layers may also be used. In one method, two piece flexible circuit tape  
5 **18** is attached to elastomer pad **10** by adhesive layer **16** and includes a patterned dielectric (typically polyimide) layer **20** and a patterned conductive layer **21**. Alternatively, adhesive layers **16** and/or **24** may be absent and elastomer pad **10** applied onto a tape **18**,  
10 such as by screen printing. Two piece flexible tape **18** may be formed, for example, by plating or sputtering a conductive metal layer **21** directly onto a dielectric layer **20**. Conductive layer **21** may be patterned by selective plating or plate and etch methods.  
15 Conductive layer **21** is formed, for example, by sputtering conductive metal directly onto dielectric layer **20**. Dielectric layer **20** is patterned with openings (or vias) **22** for accepting solder balls (or bumps) **14** so that solder balls **14** make electrical  
20 contact with patterned conductive layer **21**.

As shown in FIG. **1**, adhesive layer **16** may deform (or be compressed) between the patterned conductive material of layer **21** and elastomer pad **10**, while at the same time filling spaces between elastomer pad **10** and  
25 dielectric layer **10** in those areas where patterned conductive material is not present. For example, adhesive layer **16** may be a thickness of about 2 mils before deformation and be compressed to a thickness of between about 0.5 mil and about 1.5 mils between  
30 patterned conductive layer **21** and elastomer pad **10**. Semiconductor die **12** is attached to elastomer pad **10** by adhesive layer **24**. In the chip scale package design shown in FIG. **1**, inner lead bonding is provided between circuit leads **42** and die pads **44**. Edges of the

semiconductor die **12**, including the inner lead bonding areas, are encapsulated with encapsulant **46** which is contained within encapsulant dams **48**.

In the conventional chip scale package design of FIG. **1**, elastomer pad **10** is typically an elastomer with a relatively low modulus that is employed to isolate or "decouple" the integrated circuit from solder joints made to a PCB or other substrate in an attempt to reduce the stress on the solder joint and increase circuit reliability over periods of thermal cycling. However, in conventional chip scale package designs such as that shown in FIG. **1**, selection of a suitable elastomer is often difficult. This is because it is difficult to find elastomer materials which meet the stringent requirements of integrated circuit packaging. Moreover, processes for attaching elastomer pads to other circuit components are typically rife with challenges, such as achieving accurate placement or dealing with the typical messiness of screen printing and curing. Typical elastomer materials utilized include silicone based materials and low modulus epoxies.

FIG. **2** shows another conventional chip scale package integrated circuit design using three layer flexible circuit tape and "punched" vias. In FIG. **2**, a relatively thick dielectric layer **220** is bonded to a patterned conductive circuit layer **216** using an adhesive layer **217** to form a three layer tape. A relatively thick polymer covercoat layer **211** is deposited directly onto three layer tape **218** and attached to semiconductor die **212** with adhesive layer **224**. Covercoat layer **211** is typically a polymeric material having a thinner cross section (around 1 mil), but higher modulus than the elastomer pad **10** of FIG. **1**. Typically, covercoat **211** is an epoxy based material.

In this conventional application, the three layer tape/flex circuitry combination is typically configured as a "strip" and is fairly rigid so that the strip may be removed and placed into a fixture for overmolding of a die without bending bond wires **240** during the transfer step.

Still referring to FIG. **2**, voids may form in adhesive layer **224** due to moisture which has released from polymer layers, such as dielectric layer **220** (typically a polyimide) and covercoat **211** upon curing of die attachment adhesive **224** (typically performed at around 150°C). Further creation of voids typically occurs during solder reflow attachment of solder balls **214** to a substrate such as a PCB board **236**. Also possible is the formation of thermal cracks formed in solder balls **214**. Thermal cracks are typically caused by thermal stress generated between die **212** and attached substrate **236**. Such thermal cracking may be the cause of premature failure of solder ball joints **238**.

### **Chip Scale Package Assemblies with Nonpolymer Support Structures**

In embodiments of the disclosed method and apparatus, a nonpolymer support structure (or pad) is used between a semiconductor device or integrated circuit (such as a semiconductor die) and accompanying circuitry to provide a substantially rigid and planar surface, and to separate or decouple the die from a substrate, such as a PCB. In a typical embodiment, adhesive materials are also employed between a nonpolymer support structure and adjacent components of a chip scale package assembly for purposes of attachment and to further decouple a die and substrate. Typically, a nonpolymer support structure having a

coefficient of thermal expansion (CTE) close to that of the substrate is employed to minimize thermal stress effects on solder joints.

FIG. 3 shows a cross-sectional view of a chip scale package design according to one embodiment of the disclosed method and apparatus having a nonpolymeric support structure **50** disposed between a semiconductor die **52** and an intermediate circuit comprising two layer flexible circuit tape (or flex circuit or TAB tape) **58**. In this embodiment, nonpolymer support structure **50** is structurally coupled to the die **52** by means of adhesive layer **64**. As used herein, "structurally coupled" means two components are directly coupled or indirectly coupled (e.g., with intervening layers or other components positioned between) using any suitable means (such as by deposition, with adhesive, or other forms of bonding). As shown in FIG. 3, semiconductor die **52** typically has die bond pads or contacts **84**. A second adhesive layer **56** attaches nonpolymer pad **50** to the flexible tape **58**. Although FIG. 3 illustrates an embodiment of a chip scale package design employing two layer flexible circuit tape, it will be understood with benefit of the present disclosure that embodiments employing other types of intermediate circuitry, for example, nonflexible circuit strips or flexible circuit tapes having three or more layers are also possible. For example, one embodiment employing three layer tape **19** and wire bonding is illustrated in FIG. 3C. In this embodiment, three layer tape **19** includes dielectric layer **60**, conductive layer **59**, and second dielectric layer (typically polyimide) **60a**. Adhesive layer **60b** is employed between layers **59** and **60a**.

Intermediate circuitry typically includes an array of interconnects for electrical connection to a substrate, such as a PCB. In the embodiment



illustrated in FIG. 3, two layer flexible circuit tape 58 typically includes a patterned dielectric layer 60, and a patterned planar conductive layer 59 having individual conductive bonding pads 59a. Solder ball  
5 conductive pads 59a are typically from about 200 microns to about 600 microns in diameter and have a pitch of between about 300 microns and about 1250 microns. Patterned conductive layer 59 may be comprised of any patternable conductive material  
10 suitable for forming substantially planar circuitry including, but not limited to, metals or conductors such as silicon and polysilicon, tungsten, titanium, aluminum, aluminum based metals (such as aluminum alloys), copper, and alloys and combinations thereof,  
15 etc. (for purposes of this disclosure the term "metals" is defined to include metals, refractory metals, intermetallics, and the like or combinations thereof). Most typically patterned conductive layer 59 is copper. Patterned dielectric layer 60 may be comprised of any  
20 patternable dielectric material suitable for insulating conductive layer 59 including, but not limited to, polyimide or polyester. Most typically dielectric layer 60 is a polyimide, such as "DUPONT KAPTON" or "UBE UPILEX." Patterned conductive layer 59 typically  
25 has a thickness of between about 0.5 mils to about 1.5 mils. Patterned dielectric layer 60 typically has a thickness of between about 1 mils to about 3 mils.

To form a ball grid array 57, conductive solder balls (or bumps) 54 are attached to flexible tape 58  
30 and make electrical contact with individual pads 59a through openings (or vias) 62 patterned in dielectric layer 60. Openings 62 are patterned in a manner complementary with conductive pads 59a so that each opening 60 overlays a respective conductive pad 59a.

Solder balls **54** may be any shape and dimension suitable for making connection with bonding pads **59a** through openings **62**. Typically, solder balls **54** are substantially spherical in shape and have a diameter of  
5 from about 250 microns to about 750 microns, most typically between about 300 microns and about 600 microns. Solder balls are typically reflow attached using conventional ovens such as IR, convection, or vapor phase. Openings **62** are sized and shaped to  
10 accept solder balls **54** in such a way that electrical contact may be made with bonding pads **59a**. Typically, openings **62** are circular and have a diameter of between about 250 microns and about 600 microns, more typically between about 300 microns and about 500 microns.  
15 Conductive solder balls may be constructed of any suitable conductive material including, but not limited to, gold, solder, or copper.

In the embodiment of FIG. **3**, patterned conductive layer **59** typically has a plurality of bonding leads **82**,  
20 each of which are electrically coupled to a conductive pad **59a**. Typically, bonding leads **82** are between about 25 microns and about 100 microns in width. Bonding leads **82** are for making electrical connection to semiconductor die **52** at die pads **84** by, for example,  
25 inner lead bonding, and are therefore configured with a similar pitch as die pads **84** and a length sufficient to allow mating between leads **82** and pads **84**. However, leads **82** may also be formed to have pads **83** for wire bonding to semiconductor die **52** using wire bonds **82a** as  
30 shown in FIG. **3A**. In either case, when each bonding lead **82** is electrically connected to a respective die pad **84**, a circuit is completed between each solder ball **54** and a corresponding die pad **84**. When so configured to form a ball grid array, each solder ball **54** is

designed to be used as an individual "pin" to electrically connect an individual die pad **84** to a corresponding substrate bonding pad **75** on a substrate **76**. The pitch of ball grid array **57** as illustrated in FIG. **6**, and of corresponding substrate bonding die pads **75**, is typically between about 300 microns and about 1250 microns. Typically a substrate is a printed circuit board ("PCB"), but may also be any other circuitry including, but not limited to, flex circuitry, silicon, wafers, etc.

As shown in FIG. **3**, edges of die **52** and inner lead connection areas are typically encapsulated by encapsulant **86** which is contained by encapsulating dams **88**. Encapsulant **86** may be any suitable encapsulant known to those of skill in the art including, but not limited to, epoxy resin and silicone. Encapsulant dams **88** may be any suitable encapsulant containment structure including, for example, epoxy, adhesive tape, etc. Although the embodiment illustrated in FIG. **3** illustrates a chip scale package design employing a single patterned conductive layer **59**, it will be understood with benefit of the present disclosure that embodiments having two or more patterned (or non-patterned) conductive layers are also possible.

In the embodiment of FIG. **3**, nonpolymer pad **50** may be any material suitably rigid to facilitate processing and/or having a coefficient of thermal expansion close to that of a substrate in order to minimize stress on solder joints. By using such a nonpolymer pad configuration, formation of voids in die attachment adhesive **64** may be reduced or substantially eliminated. This is because die **52** is bonded directly to nonpolymer pad **60**, with adhesive **64** and therefore moisture from polymer materials is not present and cannot enter at the interface between these two components.

In addition to reducing thermal stress and void formation, the nonpolymer pad configuration of the disclosed method and apparatus provides other significant advantages. For example, chip scale  
5 package strips including a nonpolymer support structure  
10 provide a surface having improved flatness or surface uniformity over conventional elastomer pads. Flatness of a grid array support structure surface is an important factor toward ensuring that all solder  
10 balls **54** contact pads **75** on a substrate **76**. Desirably, a chip scale package support structure has a coplanarity of about 2 mils or less, most desirably of about 1 mil or less. Such coplanarity is difficult to achieve using conventional soft elastomer pads. A  
15 nonpolymer support structure provides a more planar surface for solder ball attachment and therefore allows a more reliable connection between a semiconductor die and a substrate.

In addition to the benefits described above, a  
20 thermally conductive nonpolymer (such as a metal sheet or foil) may be used as nonpolymer support structure **50** to provide a good thermal path for dissipation of heat from the face of semiconductor die **52** in FIG. **3** (or from the backside of semiconductor die **52** in FIG. **3A**).  
25 Such a thermally conducting nonpolymer support structure **50** may also conduct heat efficiently to the solder balls **54**.

One type of thermally conductive nonpolymer typically employed is a metal sheet or foil, with  
30 copper being a particularly well suited metal for this purpose. In addition to thermal conductance, a metal sheet may also provide improved electrical shielding of conductor layers **59** and may help minimize crosstalk. In addition, a metal sheet offers a surface that is  
35 suitable for use as a ground plane. Thus, a metal

sheet may also be used to provide a convenient ground plane (or power plane if desired), such as by direct electrical connection of a solder ball **54a** to the metal sheet **53** as shown in FIG. **3B**. This may be done, for example, through a via **55** in a conductive pad **59b** and the underlying adhesive layer **56** so that selected ground connection solder balls **54a** may electrically connect to the metal sheet **53**. The ground pads on the die may then be connected to the ground solder balls **54a** through inner leads or by wire bonds **82b** as shown in FIG. **3B**. Advantageously, when a metal sheet such as a copper foil is employed, these advantages may be achieved with relatively minimal cost. Suitable metal sheets include any patterned metal foil which supplies sufficient rigidity and/or thermal expansion qualities including, but not limited to metal foils made of copper, stainless steel, alloy 42, tungsten, titanium, aluminum, aluminum based metals (such as aluminum alloys), and alloys and combinations thereof, etc.

Copper foil may also be coated with a thin plating for bonding to provide good solderability, low cost, and/or reduced oxidation. Examples of suitable coatings include, but are not limited to, a surface coating of plated nickel, nickel/boron, black copper oxide, tin/lead (such as a high lead content tin/lead alloy of over about 37% lead, or precious metals, such as silver or gold. Most typically, a nonpolymer support structure is a patterned copper foil having a thickness of between about 4 mils and about 10 mils, more typically between about 5 mils and about 7 mils. Copper alloys typically used for lead frames, such as 194, are well suited for this application.

Advantageously, when a nonpolymer pad of suitable rigidity is employed, a chip scale package strip may be handled with typical magazine feeding equipment

commonly used for lead frames. By "suitable rigidity" it is meant that a modulus greater than about 1 Mpsi ( $1 \times 10^6$  pounds per square inch). Examples of nonpolymer materials having suitable rigidity include ceramic, and metal foils such as those described above. However, it will be understood that benefits of the disclosed method and apparatus may also be realized using nonpolymer materials having a modulus less than about 1 Mpsi. Such benefits include those described elsewhere herein.

Referring to FIG. 3, adhesive layers 56 and 64 may be any adhesive suitable for securing nonpolymer pad 50 to flexible tape 58 and semiconductor die 52. Typically, adhesive layers 56 and 64 are selected from dielectric materials that act with a nonpolymer pad 50 to isolate or "decouple" die 52 from a substrate (or PCB) 76, thus further relieving stress on solder joints and providing improved reliability. Such adhesives also act to provide a small amount of Z-axis compliance for socketing. Examples of suitable adhesives include, but are not limited to, an acrylate PSA, a thermoplastic polyimide (such as DuPont "KJ" material), a polyolefin, DuPont "PYRALUX", epoxy resins, and mixtures thereof. Most typically, thermoplastic polyimide is employed as adhesive layers 56 and 64.

Adhesive may be applied to a nonpolymer pad in any thickness suitable for forming a bond between the elastomer pad and adjacent surfaces, such as a die or circuit tracing. Typically, adhesive layers 56 and 64 have a thickness of between about 1 mil and about 3 mils, more typically between about 1 mil and about 2 mils.

Although the illustrated embodiments employ a single nonpolymer support structure, it will be understood with benefit of the present disclosure that

more than one nonpolymer support structure may be employed in a laminated chip scale package tape assembly. For example, two or more electrically isolated metal support structures may be employed and  
5 used to form separate circuit paths (such as both ground and power planes), or combinations of metal and nonmetal nonpolymer support structures are also possible, such as epoxy printed circuit board material.

In an alternative embodiment illustrated in FIG.  
10 **3D**, a mounting layer **351** may be patterned with a layer of deposited nonpolymer material **350** and employed between a semiconductor die **352** and accompanying circuitry. For example, mounting layer **351** may be adhered to two layer flexible circuit tape **318** or other  
15 intermediate circuitry with adhesive layer **356**, and to semiconductor die **352** with adhesive layer **364**. When employed instead of the nonpolymer support structure embodiments previously described, embodiments of nonpolymer layer **350** act to reduce or substantially  
20 eliminate void formation by substantially preventing moisture from escaping into die attachment adhesive **364**. Advantageously, a mounting layer patterned with nonpolymer material may be manufactured in many ways including, but not limited to, as a separate tape  
25 component, or as attached to a TAB tape. In some cases, the use of a mounting layer patterned with nonpolymer material may be less expensive than embodiments of the nonpolymer support structure previously described.

30 Still referring to FIG. **3D**, nonpolymer layer **350** may be composed of any nonpolymer material suitable for preventing the migration of moisture into adhesive layer **364**, including those materials listed for use as a nonpolymer support structure. Mounting layer **351** may  
35 be any material suitable for patterning or deposition

of nonpolymer layer **350**, including those dielectric materials listed for use as patternable dielectric materials. Likewise, adhesive layers **356** and **364** may be any suitable adhesive or attachment means, including  
5 those listed for use with nonpolymer support structures. Typically nonpolymer layer **350** is a copper layer having a thickness of between about 1  $\mu\text{m}$  and about 20  $\mu\text{m}$ , and mounting layer **351** is a polyimide layer having a thickness of between about 1 mil and  
10 about 3 mils. Most typically, nonpolymer layer **350** is a copper layer having a thickness of between about 5  $\mu\text{m}$  and about 10  $\mu\text{m}$ , and mounting layer **351** is a polyimide layer having a thickness of about 2 mils.

FIG. **3D** illustrates the use of a mounting layer  
15 **351** patterned with a nonpolymer layer **350** in an application similar to that shown in FIG. **3A** for a nonpolymer support structure. As with embodiments of nonpolymer support structures, many variations are possible to the configuration illustrated in FIG. **3D**.  
20 For example, a conductive nonpolymer layer **350** may be used as a ground plane, power plane or to complete other types of circuit paths, such as in a manner similar to that illustrated in FIG. **3B** for a nonpolymer support structure. A mounting layer **351** and nonpolymer  
25 layer **350** may also be employed with intermediate circuitry having three or more layers, such as similar to the embodiment illustrated in FIG. **3C** for nonpolymer support structures. In addition, more than one nonpolymer layer **350** may be employed.

30

### **Manufacture And Assembly Of Chip Scale Package Components**

A chip scale package device of the disclosed method and apparatus having a nonpolymer support



structure (or "pad") may be formed in a number of ways and for use in a number of different applications. For example, one method of constructing chip scale package tape having a nonpolymer pad includes the steps of

5 laminating an adhesive onto a roll of nonpolymer material (such as metal foil), punching or stamping the nonpolymer material in a desired shape, and aligning and adhering flexed circuitry (or circuit tracing) to the nonpolymer to form a chip scale package tape (such

10 as in the form of a strip). In the alternative, a chip scale package tape may be formed by punching a nonpolymer material (such as a metal foil) to a desired shape, punching an adhesive film to the same shape, aligning both film and foil with circuitry tracing, and

15 laminating the structure. In either case, alignment of the circuit tracing to a nonpolymer support structure is accurate, yet relatively inexpensive. A variety of different steps may be performed using the chip scale package strip or tape just described to form a chip

20 scale package device. These steps may include die attachment, wire and/or inner lead bonding, overmolding and/or solder ball attachment steps. Advantageously, assembly of chip scale package devices according to these processes is relatively efficient,

25 straightforward, and cost effective.

FIG. 4 illustrates lamination of adhesive layers **56** and **64** to both sides of a thin roll of copper sheet (or foil) **50**. Typically, adhesive laminate having a coversheet (or release liner) is employed, and the

30 release liner is left on the side of adhesive layers **56** and **64** facing away from the copper foil **50**. Suitable adhesive laminates incorporating release liners include acrylate PSA type adhesives. As shown in FIG. 4, laminate adhesive used to form adhesive layers **56** and

35 **64** is typically applied using roll laminates **100**.

However, it will be understood with benefit of the present disclosure that adhesives, such as those previously mentioned, may be applied using any suitable method including, but not limited to, screen printing  
5 and spray deposition.

FIG. 5 shows a top view of a nonpolymer sheet 50 that has been laminated with adhesive layers 56 and 64. In FIG. 5, nonpolymer sheet 50 has been punched or stamped to form patterns having die squares 51  
10 surrounded by connection slot regions 110. Die squares 51 are configured to have a shape complementary to a semiconductor die 52 and are smaller in area to allow clearance for connection of leads 82 (or wire bonds) to die pads 84 in the connection slot regions 110.  
15 Connection slots 110 provide space for connection to die pads 84 using inner lead bonding, wire bonding, or other suitable connection methods. Taken together, the dimensions of die squares 51 and connection slots 110, provide individual platforms for semiconductor dies 52.

20 It will be understood with benefit of the present disclosure that stamping or punching operations in the disclosed method may be performed using any punching or stamping method suitable for integrated circuit packaging. The nonpolymer sheet can also be patterned  
25 by chemical etching, using a steel rule die, or using a chem etched die. Tooling holes 112 are also punched in the sheet 50 to aid in the accurate alignment of circuitry.

Next, as shown in FIG. 6, flexible tape 58 having  
30 vias 62 for accepting solder balls is aligned with the use of tooling holes 112 and laminated to one side of copper sheet 50. Lamination of circuitry may be accomplished in a number of ways, including in a roll-to-roll process (such as a roll-to-roll process using

sprocket holes), or in a press. In this embodiment, prior to lamination the release liner is typically pulled off the adhesive layer **56** and a panel or strip of circuits is laminated to the sheet **50** using tooling  
5 holes **112** for alignment. However, other adhesive and lamination methods, such as those mentioned previously, may be employed.

At this point, attachment and bonding of an integrated circuit die may continue uninterrupted, or  
10 the nonpolymer sheet **50** and the attached flexible tape **58** may be shipped elsewhere for further assembly. In the latter case, the nonpolymer sheets **50** and the attached flexible tape **58** are typically cut into a strip format prior to shipping. In a strip format, a  
15 single chip scale package strip typically has numerous individual die squares **51**. In either case, further assembly typically involves removal of the second release liner from adhesive layer **64** in preparation for mounting a die onto the nonpolymer sheet **50**. In the  
20 case of strip format processing, strips of nonpolymer sheets and attached circuitry are loaded into magazines for processing. Die are then typically placed on the tacky side of the nonpolymer strip (opposite the side with the circuitry) and cured if necessary. However,  
25 it will be understood with benefit of this disclosure that a die may also be picked and placed onto a roll of nonpolymer sheets (as opposed to a strip), and that a semiconductor die may be placed with its circuitry level adjacent or opposite the nonpolymer sheet. The  
30 die side of the nonpolymer strip may also be left bare of adhesive and a die attached adhesive (typically epoxy based materials) used for attachment of the die.

Next, the strips (including circuitry and one or more dies) are typically flipped and placed into  
35 standard magazines which are loaded into, for example,

a wire bond machine or a thermocompression bond machine  
As shown in FIG. 7, each lead **120** from the tape is  
bonded to a die pad **122** using, for example, a bonding  
tool **124**. A fixture **126** is used to support the tape  
5 (including the dies) so as to allow the leads **120** to  
break at a frangible portion (or notch) **126** during the  
bonding process. As shown in FIG. 8, the strip may  
then be overmolded by filling in the slots **110** with  
encapsulant **132**. Typically the encapsulant is  
10 contained by dam features **130** and cured using a  
suitable curing method such as, for example, UV or  
thermal methods. Alternatively, as shown in FIG. 9,  
the strips may be flipped over onto a fixture surface  
**140** and the slots **110** filled with encapsulant **132** from  
15 the die side of the strip without need for encapsulant  
dam features. As shown in FIGS. 3A and 3B, a die **52**  
may also be connected to a circuit trace layer **59** using  
wire bonds **82a** such as, for example, when a  
semiconductor die is "flipped" so that the circuit  
20 layer and die pads of a semiconductor die are oriented  
in a direction facing away from the support structure.  
An overhead view of such an embodiment is shown in FIG.  
**6A**.

As shown in FIG. 10, solder balls (or bumps) **54**  
25 may next be mounted within openings (or vias) **62**  
formed, for example, by etching openings within a  
polyimide layer **60**. Solder balls **54** may be attached to  
strips using any method suitable for forming a secure  
electrical connection between the balls **54** and the  
30 conductive bonding pads **59a** including, for example,  
heating and reflow using any conventional means such as  
IR, convection, or vapor phase. Although not shown,  
vias **62** may also be processed as plated through holes

(PTH) and/or be filled with a separate conducting filler material prior to solder ball attachment.

At this point, a strip or roll may be cut to form single or multiple die chip scale package packages (a  
5 single die package **150** is shown in FIG. **10**). This may be accomplished using any suitable excision method such as, for example, punching, cutting, or other similar process.

It will be understood with benefit of the present  
10 disclosure that other chip scale package configurations may also be fabricated using this method, including packages having more than one semiconductor dies. In addition, non-chip scale package configurations, such as conventional BGA packages, may be manufactured using  
15 the disclosed method and apparatus concepts. It will also be understood that although the methods just described and illustrated are for manufacturing integrated circuits using a strip format, benefit of these methods may also be obtained when used to  
20 manufacture integrated circuits using other processes and formats, including, but not limited to, integrated circuits formed using a roll-to-roll (or reel-to-reel) format. In this way benefits of the disclosed method and apparatus may be realized in formats compatible  
25 with existing industry infrastructure and with newer formats currently being employed or developed. It will also be understood that the aforementioned packaging process may be performed while with a die still in wafer form. For example, a nonpolymer sheet may be  
30 aligned and adhered directly to a wafer and chip bonding performed. As before, slots may then be filled in with encapsulant, solder balls attached, and individual package pieces punched or sawed out.

While the invention may be adaptable to various  
35 modifications and alternative forms, specific embodiments have been shown by way of example and

described herein. However, it should be understood that the invention is not intended to be limited to the particular forms disclosed. Rather, the invention is to cover all modifications, equivalents, and  
5 alternatives falling within the spirit and scope of the invention as defined by the appended claims.

**WHAT IS CLAIMED IS:**

1. A package for an integrated circuit, comprising:
  - 5 an intermediate circuit including an array of electrical interconnects; and
  - at least one nonpolymer layer having first and second sides, said first side of said layer being structurally coupled to said  
10 integrated circuit, and said second side of said layer being structurally coupled to said intermediate circuit.
- 15 2. The package of claim 1, wherein said integrated circuit has a plurality of electrical contact sites, said contact sites being electrically coupled to said electrical interconnects of said intermediate circuit.
- 20 3. The package of claim 2, wherein said electrical contact sites of said integrated circuit are wire bonded to said electrical interconnects of said intermediate circuit.
- 25 4. The package of claim 2, wherein said electrical contact sites of said integrated circuit are thermocompression bonded to said electrical interconnects of said intermediate circuit.
- 30 5. The package of claim 1, wherein said nonpolymer layer is conductive and wherein said nonpolymer layer is electrically coupled to said integrated circuit to form a power or ground plane.

6. The package of claim 1, wherein said nonpolymer layer is a nonpolymer support structure having a modulus of greater than about 1 Mpsi.

5 7. The package of claim 1, wherein said nonpolymer layer is a nonpolymer support structure comprised of a metal foil having a thickness of between about 4 mils and about 10 mils.

10 8. The package of claim 1, wherein said nonpolymer layer is a nonpolymer support structure comprised of a copper foil.

9. The package of claim 1, further comprising a  
15 mounting layer having first and second sides, said first side of said mounting layer being structurally coupled to said second side of said nonpolymer layer, and said second side of said mounting layer being structurally coupled to said intermediate circuit.

20

10. The package of claim 9, wherein said mounting layer is a polyimide layer having a thickness of between about 1 mil and about 3 mils, and wherein said  
25 nonpolymer layer is a copper layer having a thickness of between about 1  $\mu\text{m}$  and about 20 $\mu\text{m}$ .

11. The package of claim 1, wherein said intermediate  
30 circuit is a flexible circuit.

12. The package of claim 1 wherein said intermediate circuit has first and second sides, said first side of



said intermediate circuit being structurally connected to said second side of said nonpolymer layer; and

5 further comprising a plurality of solder balls or bumps electrically coupled to said intermediate circuit; said plurality of solder balls or bumps being structurally coupled to said second side of said intermediate circuit.

10

13. A method of forming a package for an integrated circuit comprising the steps of:

15 providing an intermediate circuit including an array of electrical interconnects;

providing at least one nonpolymer layer having first and second sides; said first side of said nonpolymer layer being adapted for structural coupling to said integrated circuit; and

20

structurally coupling said second side of said nonpolymer layer to said intermediate circuit.

25

14. The method of claim 13, further comprising the step of structurally coupling said integrated circuit to said first side of said nonpolymer layer.

30

15. The method of claim 14, wherein said integrated circuit has a plurality of electrical contact sites, and further comprising the step of electrically

35

coupling said contact sites to said electrical interconnects of said intermediate circuit.

5 16. The method of claim 14, wherein the step of electrically coupling said contact sites to said electrical interconnects includes the step of wire bonding or thermocompression bonding said electrical contact sites of said integrated circuit to said  
10 electrical interconnects of said intermediate circuit.

17. The method of claim 14, wherein said nonpolymer layer is conductive and further comprising the step of  
15 electrically coupling said nonpolymer support structure to said integrated circuit to form a power or ground plane.

20 18. The method of claim 13, wherein said nonpolymer layer is a nonpolymer support structure having a modulus of greater than about 1 Mpsi.

25 19. The method of claim 13, wherein said nonpolymer layer is a nonpolymer support structure is a metal foil having a thickness of between about 4 mils and about 10 mils.

30 20. The method of claim 13, wherein said nonpolymer layer is a nonpolymer support structure comprising copper foil.

35

21. The method of claim 13 wherein said nonpolymer layer is a copper layer having a thickness of between about 1  $\mu\text{m}$  and about 20  $\mu\text{m}$ .

5

22. The method of claim 13, wherein said intermediate circuit is a flexible circuit.

10 23. The method of claim 13, wherein said intermediate circuit has first and second sides; wherein said step of structurally coupling said intermediate circuit to said nonpolymer layer includes the step of structurally connecting said first side of said intermediate circuit  
15 to said second side of said nonpolymer layer; and further comprising the step of structurally and electrically coupling a plurality of solder balls or bumps to said intermediate circuit; said plurality of solder balls or bumps being structurally coupled to  
20 said second side of said intermediate circuit.

24. An electronic package, comprising:

25 a flexible tape including a patterned conductive layer and at least one patterned dielectric layer;

a nonpolymer support structure having first and  
30 second sides, said first side of said support structure being structurally coupled to said second side of said conductive layer of said flexible tape.

35

25. The package of claim 24, wherein said conductive layer has first and second sides and is patterned to form an electrically conductive region, wherein said dielectric layer has first and second sides and is  
5 patterned to form a plurality of openings extending through said dielectric layer, each of said openings being configured to receive a solder ball, and wherein said first side of said conductive layer is joined to said second side of said dielectric layer so that said  
10 plurality of openings in said dielectric layer are aligned with at least part of said electrically conductive region of said conductive layer.

15 26. The package of claim 25, further comprising a semiconductor device having a first side structurally coupled to said second side of said nonpolymer support structure, said semiconductor device including a plurality of electrical contact sites; said contact  
20 sites being electrically coupled to said conductive layer of said flexible tape.

27. The package of claim 26, further comprising a  
25 plurality of solder balls or bumps disposed on said first side of said dielectric layer of said flexible tape, each of said solder balls or bumps being positioned in one of said plurality of openings in said dielectric layer and being electrically connected to  
30 said conductive region of said conductive layer of said flexible tape.

28. The package of claim 27, wherein said nonpolymer support structure has a modulus of greater than about 1 Mpsi.

5

29. The package of claim 27, wherein said nonpolymer support structure is a copper foil having a thickness of between about 4 mils and about 10 mils.

10

30. An electronic package, comprising:

a patterned conductive layer having first and second sides and an outer lateral boundary, said conductive layer being patterned to form an electrically conductive region having peripheral conductive features disposed around a circumference of said outer lateral boundary for electrical connection to a semiconductor device;

20

a patterned dielectric layer having first and second sides and an outer lateral boundary with a smaller circumference than said circumference of said patterned conductive layer, said dielectric layer being patterned to form a plurality of openings extending through said dielectric layer, each of said openings being configured to receive a solder ball, and wherein said first side of said conductive layer is joined to said second side of said dielectric layer so that said plurality of openings in said dielectric layer are aligned with at least part of said electrically conductive region of said

35

conductive layer and so that said peripheral conductive features of said conductive layer extend beyond the outer boundary of said dielectric member;

5

a nonpolymer support structure having first and second sides, said support structure being substantially rigid and having an elastic modulus greater than about 1 Mpsi, and said first side of said support structure being structurally coupled to said second side of said conductive layer;

10

a semiconductor device having a first side structurally coupled to said second side of said nonpolymer support structure, said semiconductor device including a plurality of electrical contact sites; at least one of said contact sites being electrically coupled to said peripheral conductive features of said conductive layer; and

15

20

a plurality of solder balls disposed on said first side of said dielectric layer, each of said solder balls being positioned in one of said plurality of openings in said dielectric layer and being electrically connected to said conductive region of said conductive layer.

25

30

31. The package of claim 30, wherein said electrical contact sites of said semiconductor device are electrically coupled to said peripheral conductive features of said conductive layer by means of wire bonds, inner lead bonds, or a mixture thereof.

35

32. The package of claim 30 wherein said nonpolymer support structure is electrically conductive and  
5 wherein said nonpolymer support structure is electrically coupled between at least one of said electrical contact sites of said semiconductor device and said conductive layer, such that said nonpolymer support structure forms an electrical circuit between  
10 said semiconductor device and said conductive layer.

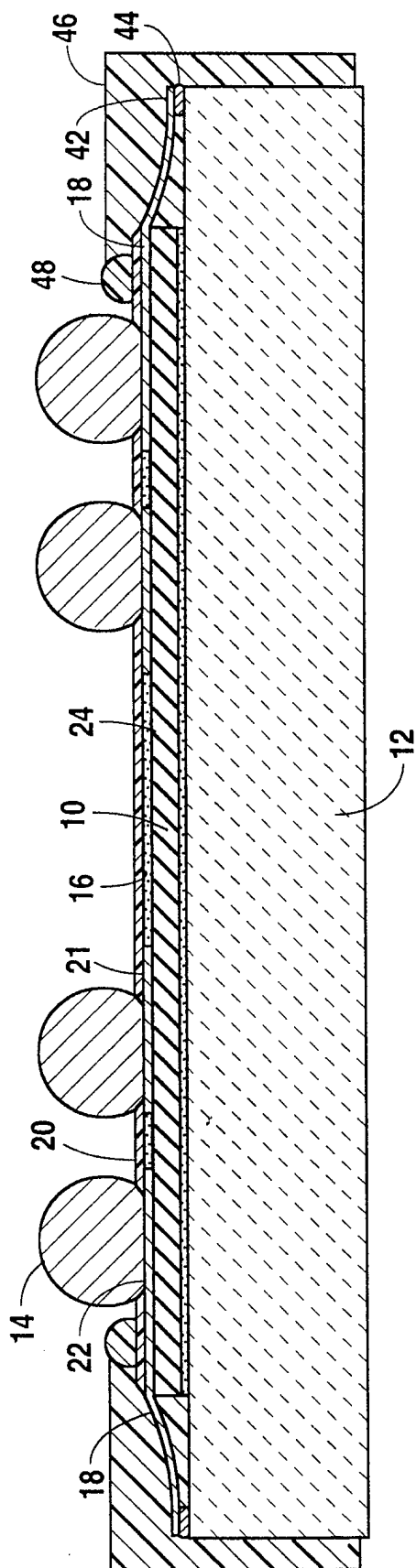


Fig. 1  
(PRIOR ART)

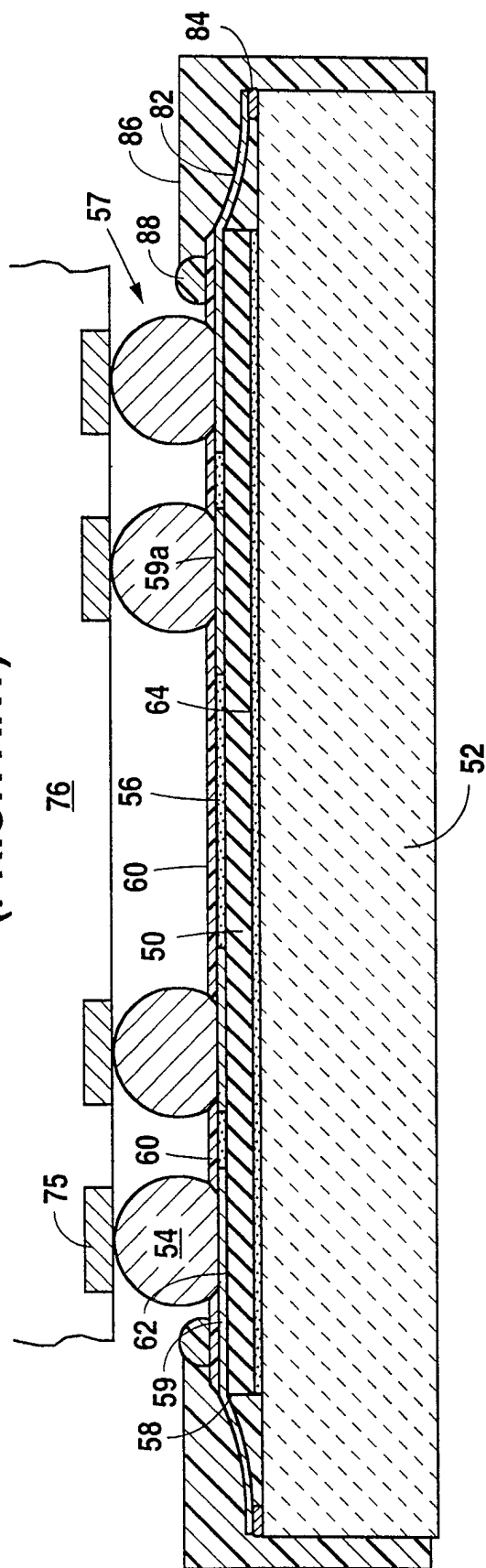


Fig. 3



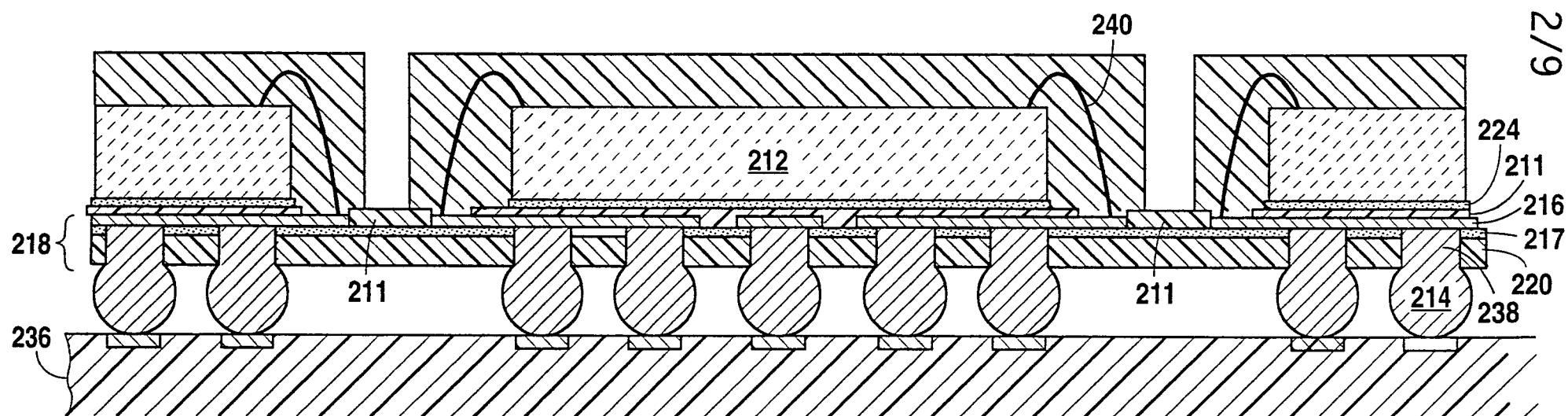


Fig. 2  
( PRIOR ART )

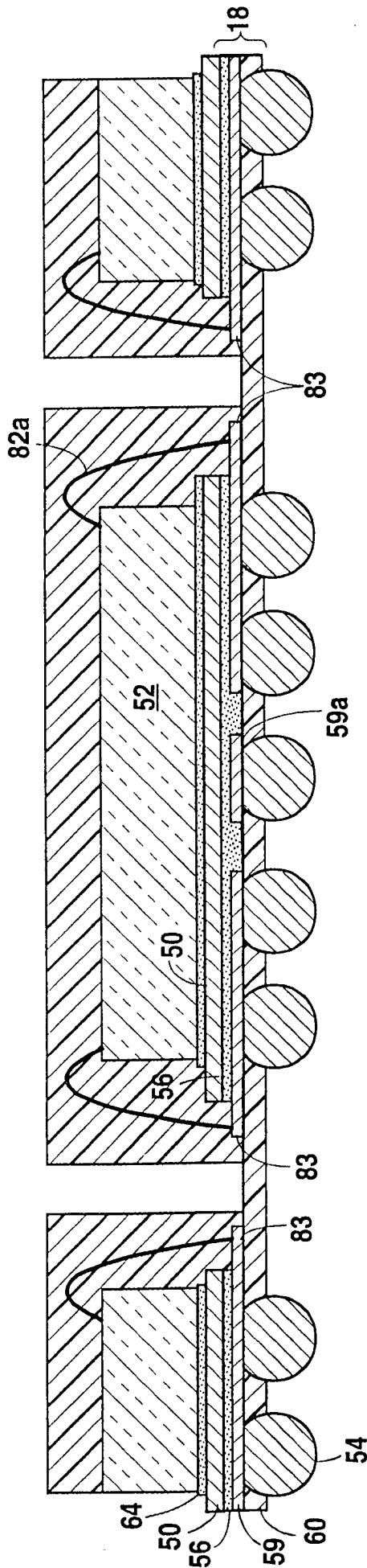


Fig. 3A

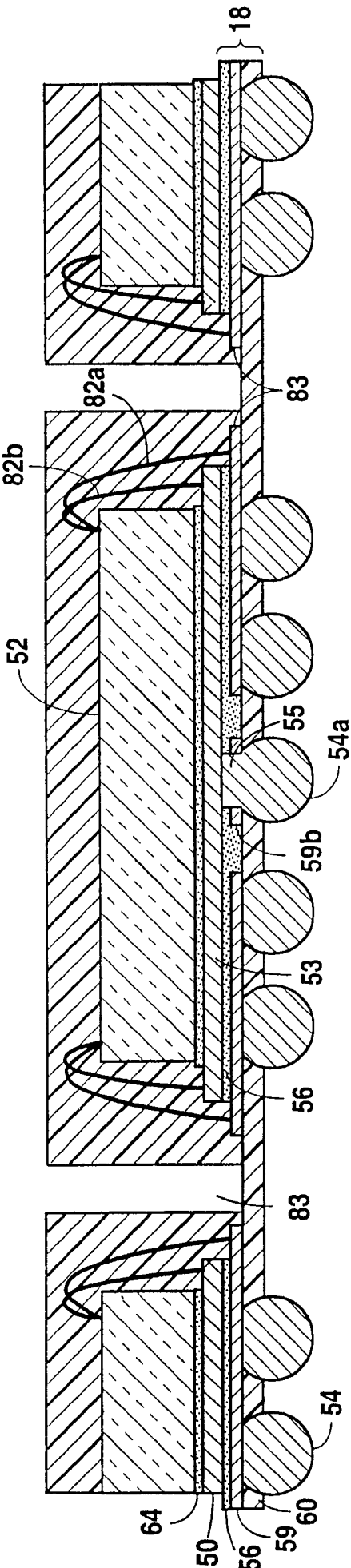


Fig. 3B

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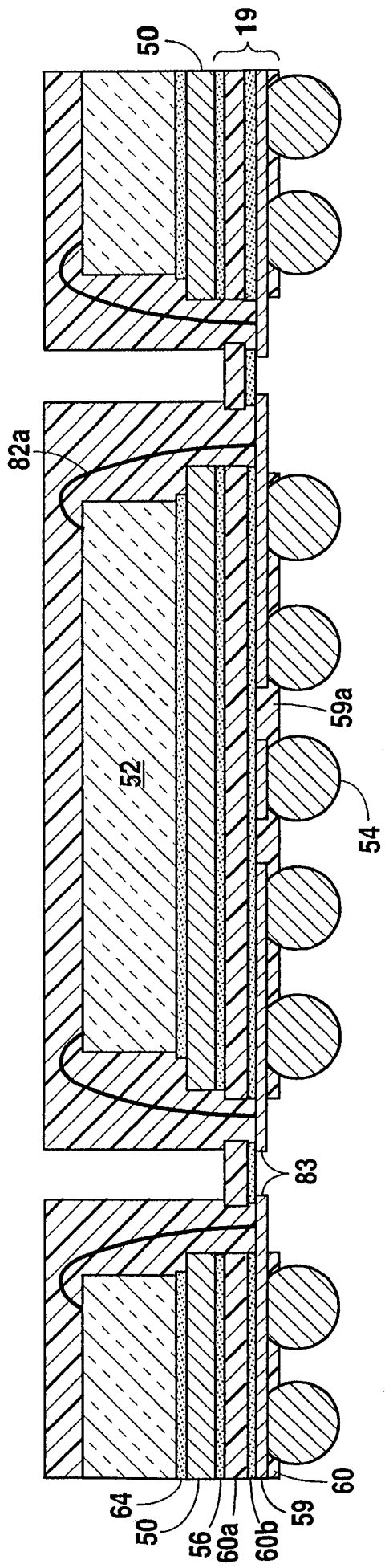


Fig. 3C

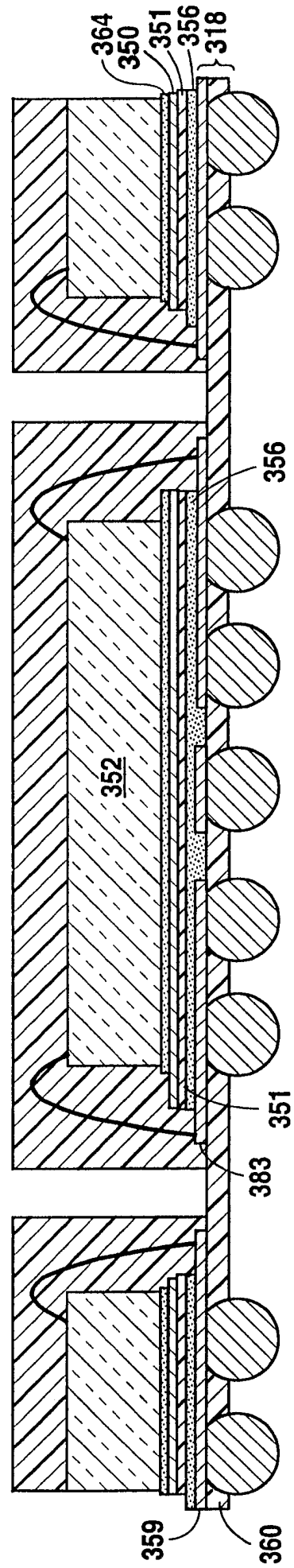


Fig. 3D

5/9

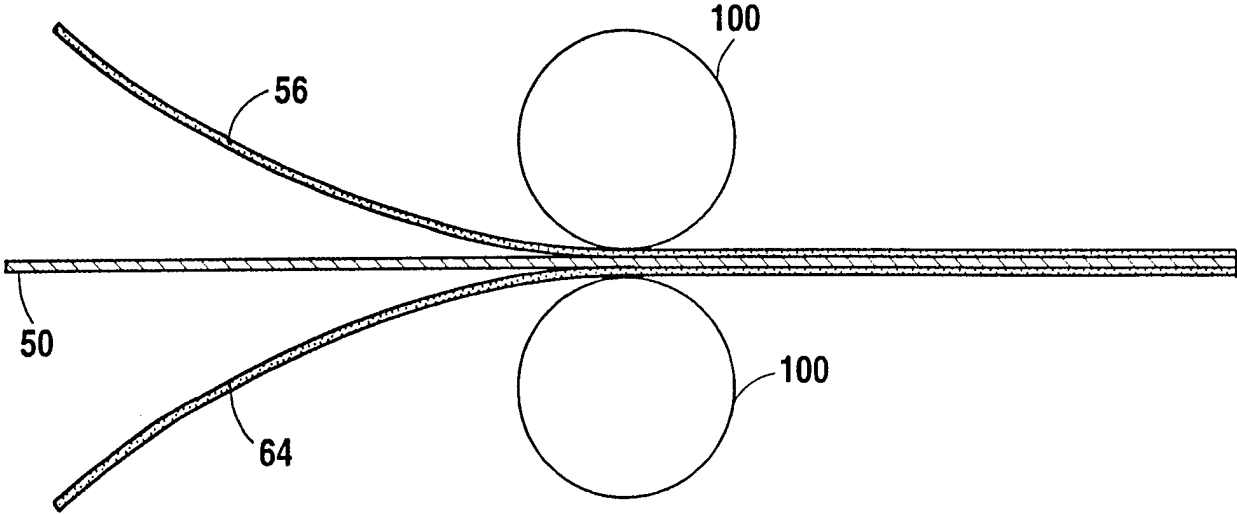


Fig. 4

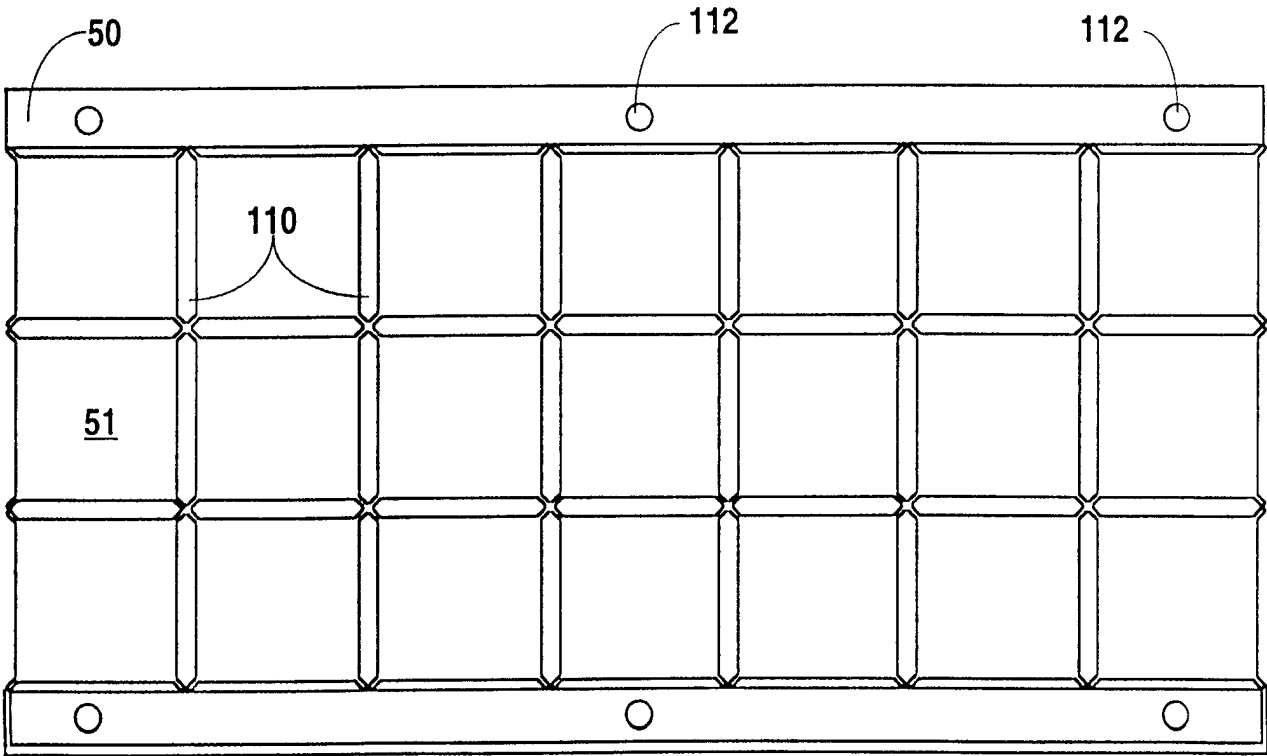


Fig. 5

6/9

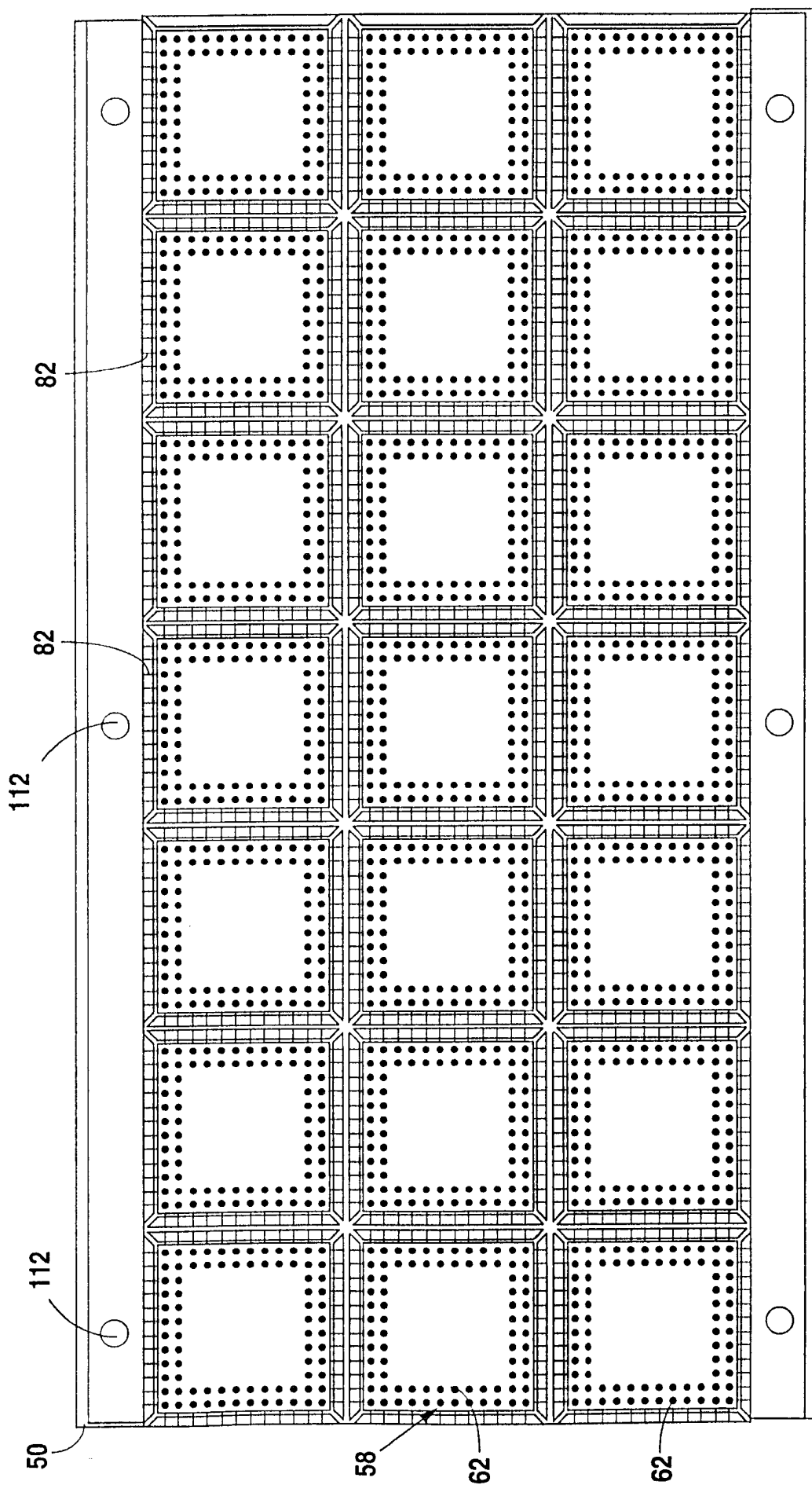


Fig. 6

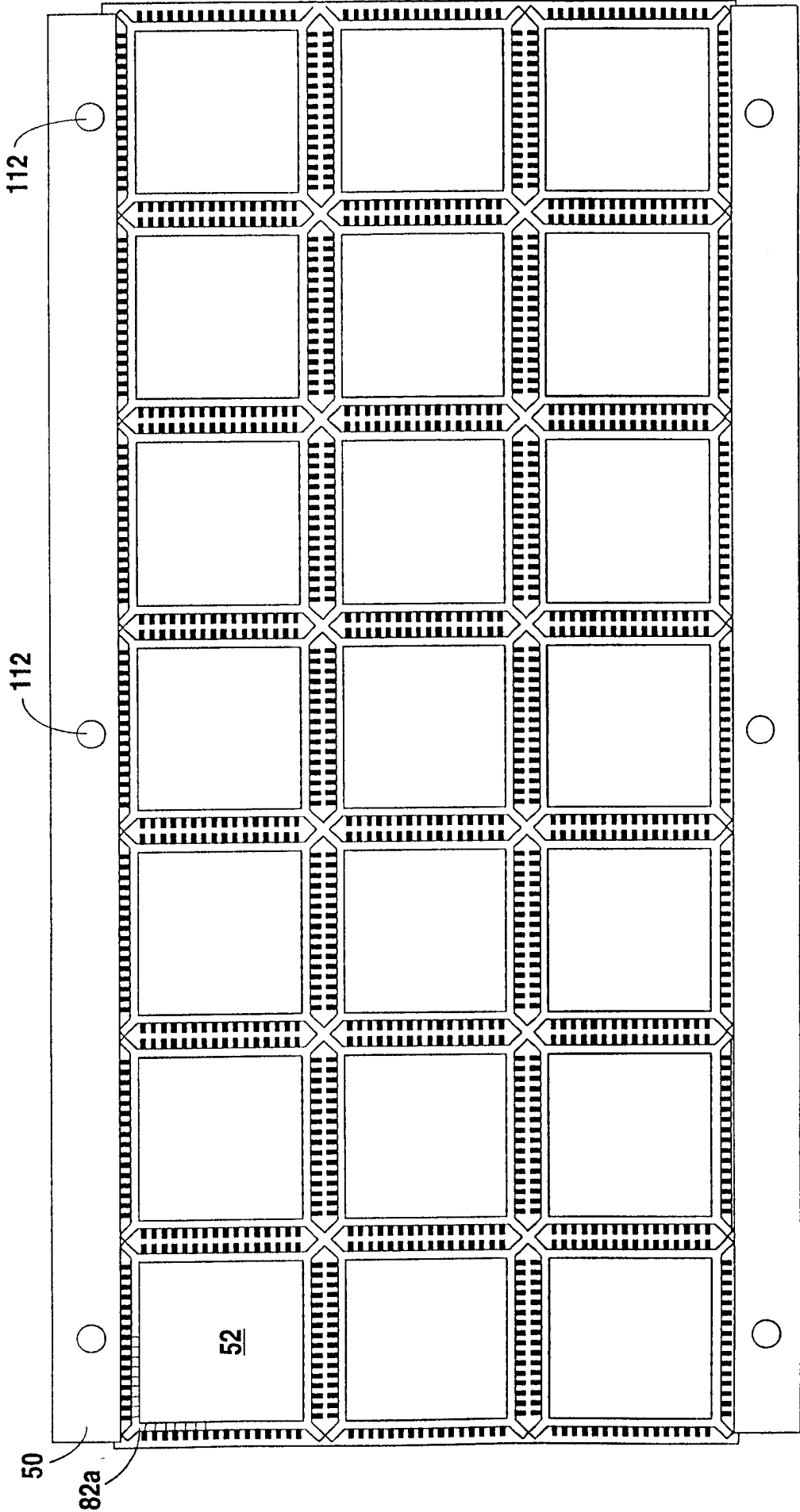


Fig. 6A

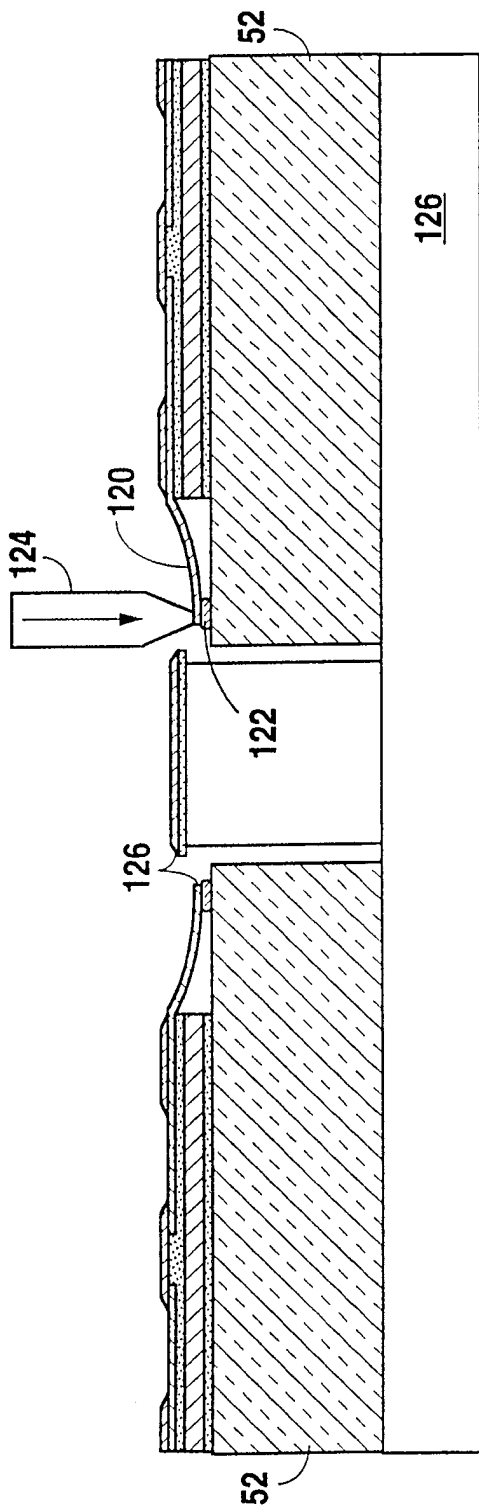


Fig. 7

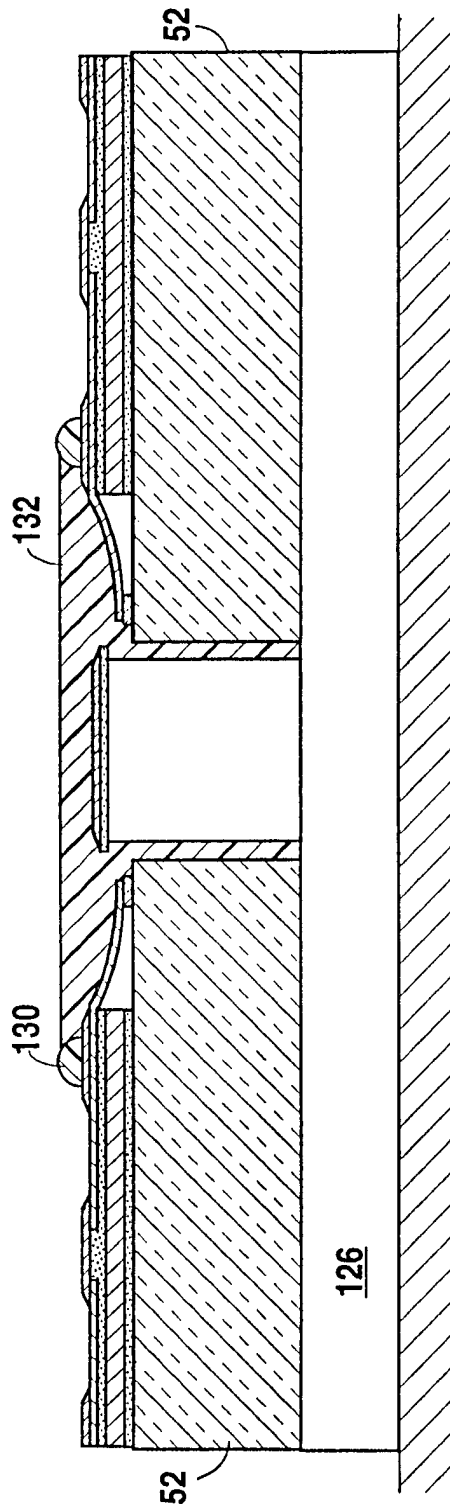


Fig. 8

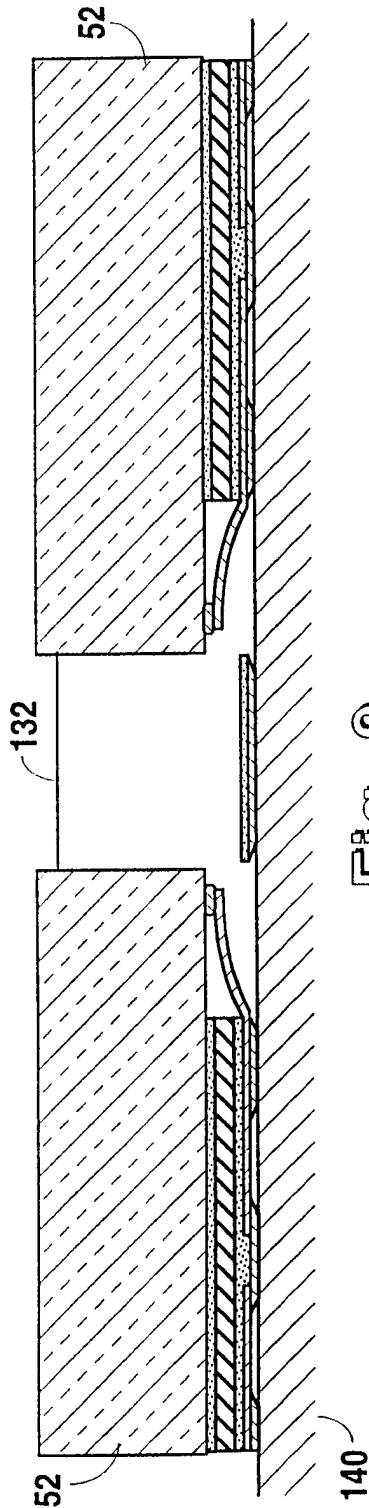


Fig. 9

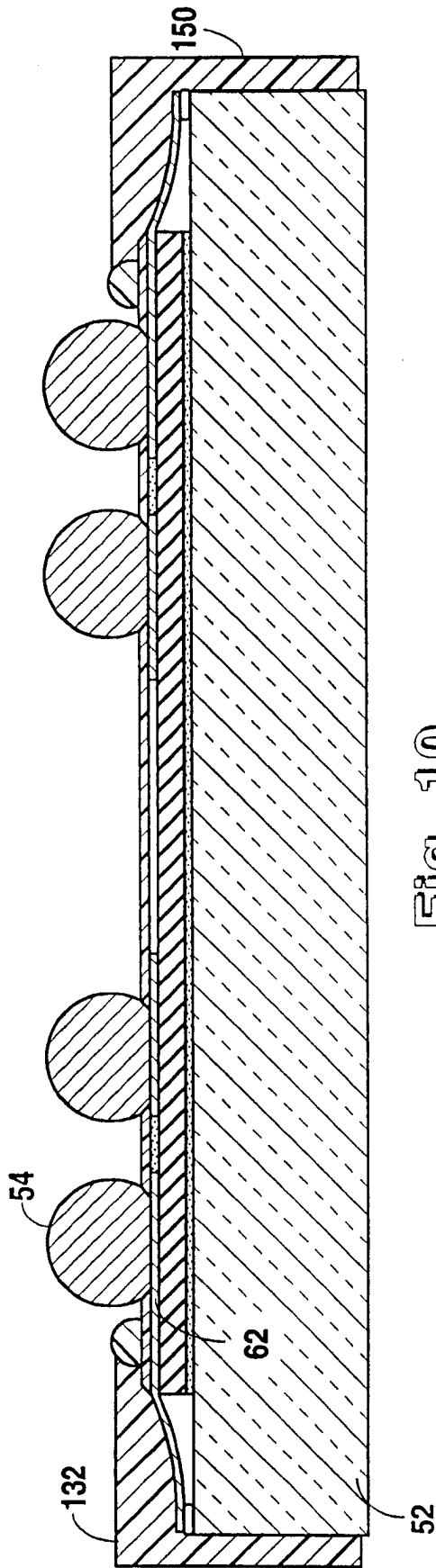


Fig. 10



# INTERNATIONAL SEARCH REPORT

Intern. al Application No  
PCT/US 97/05489

A. CLASSIFICATION OF SUBJECT MATTER  
IPC 6 H01L23/498 H01L23/00 H01L21/60

According to International Patent Classification (IPC) or to both national classification and IPC

## B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)  
IPC 6 H01L

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

## C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	FR 2 725 305 A (NIPPON ELECTRIC CO) 5 April 1996  see page 8, line 8 - line 11 see page 9, line 15 - page 11, line 26; figures 2A,2B ---	1,2,4,6, 11-15, 18, 22-28, 30,31
P,X	EP 0 751 561 A (HITACHI CHEMICAL CO) 2 January 1997	1-3,6,8, 11-16, 18,20, 22-28
P,Y	see page 11, line 30 - page 12, line 27; figures 17A-17G --- -/--	5,17,30, 31

☒ Further documents are listed in the continuation of box C.

☒ Patent family members are listed in annex.

\* Special categories of cited documents :

"A" document defining the general state of the art which is not considered to be of particular relevance  
"E" earlier document but published on or after the international filing date  
"L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)  
"O" document referring to an oral disclosure, use, exhibition or other means  
"P" document published prior to the international filing date but later than the priority date claimed

"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention  
"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone  
"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art.  
"&" document member of the same patent family

Date of the actual completion of the international search

1 August 1997

Date of mailing of the international search report

19 -08- 1997

Name and mailing address of the ISA

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## INTERNATIONAL SEARCH REPORT

 Intern al Application No  
 PCT/US 97/05489

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